

40V N-Channel MOSFETs

General Description

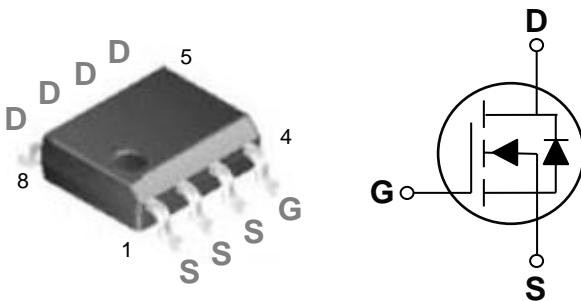
These N-Channel enhancement mode power field effect transistors are using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. These devices are well suited for high efficiency fast switching applications.

BVDSS	R _{DS(ON)}	I _D
40V	19mΩ	6.7A

Features

- 40V, 6.7A, R_{DS(ON)}=19mΩ @V_{GS} = 10V
- Improved dv/dt capability
- Fast switching
- Green Device Available

SOP-8 Pin Configuration



Applications

- Notebook
- Load Switch
- LED applications
- Hand-Held Device

Absolute Maximum Ratings (T_c=25°C unless otherwise noted)

Symbol	Parameter	Rating	Units
V _{DS}	Drain-Source Voltage	40	V
V _{GS}	Gate-Source Voltage	± 20	V
I _D	Drain Current – Continuous (T _A =25°C)	6.7	A
	Drain Current – Continuous (T _A =70°C)	5.4	A
I _{DM}	Drain Current – Pulsed ¹	26.8	A
P _D	Power Dissipation (T _A =25°C)	1.47	W
	Power Dissipation – Derate above 25°C	0.12	W/°C
T _{STG}	Storage Temperature Range	-55 to 150	°C
T _J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Unit
R _{θJA}	Thermal Resistance Junction to ambient	---	85	°C/W



FTK4910

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Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Off Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	40	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BV_{DSS} Temperature Coefficient	Reference to 25°C , $I_D=1\text{mA}$	---	0.034	---	V/ $^\circ\text{C}$
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=40V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	1	μA
		$V_{DS}=32V, V_{GS}=0V, T_J=85^\circ\text{C}$	---	---	10	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA

On Characteristics

$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10V, I_D=6A$	---	16	19	m Ω
		$V_{GS}=4.5V, I_D=4A$	---	20	25	m Ω
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\mu A$	1.2	1.5	2.5	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	-4.3	---	mV/ $^\circ\text{C}$
gfs	Forward Transconductance	$V_{DS}=10V, I_D=3A$	---	6	---	S

Dynamic and switching Characteristics

Q_g	Total Gate Charge ^{2,3}	$V_{DS}=32V, V_{GS}=10V, I_D=6A$	---	11.8	23	nC
Q_{gs}	Gate-Source Charge ^{2,3}		---	1.7	3.4	
Q_{gd}	Gate-Drain Charge ^{2,3}		---	4	8	
$T_{d(on)}$	Turn-On Delay Time ^{2,3}	$V_{DD}=20V, V_{GS}=10V, R_G=3.3\Omega$ $I_D=1A$	---	5	10	ns
T_r	Rise Time ^{2,3}		---	8	16	
$T_{d(off)}$	Turn-Off Delay Time ^{2,3}		---	17	34	
T_f	Fall Time ^{2,3}		---	5	10	
C_{iss}	Input Capacitance	$V_{DS}=20V, V_{GS}=0V, F=1\text{MHz}$	---	722	1440	pF
C_{oss}	Output Capacitance		---	83	166	
C_{rss}	Reverse Transfer Capacitance		---	61	122	
R_g	Gate resistance	$V_{GS}=0V, V_{DS}=0V, F=1\text{MHz}$	---	2.1	---	Ω

Drain-Source Diode Characteristics and Maximum Ratings

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	$V_G=V_D=0V$, Force Current	---	---	6.7	A
I_{SM}	Pulsed Source Current		---	---	13.4	A
V_{SD}	Diode Forward Voltage	$V_{GS}=0V, I_S=1A, T_J=25^\circ\text{C}$	---	---	1	V

Note :

1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
2. The data tested by pulsed , pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
3. Essentially independent of operating temperature.

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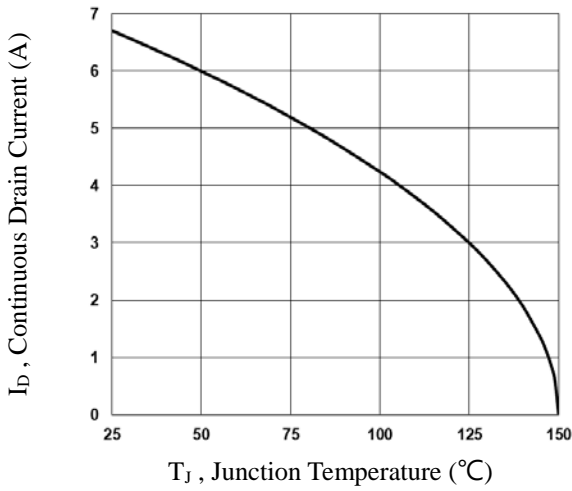


Fig.1 Continuous Drain Current vs. T_J

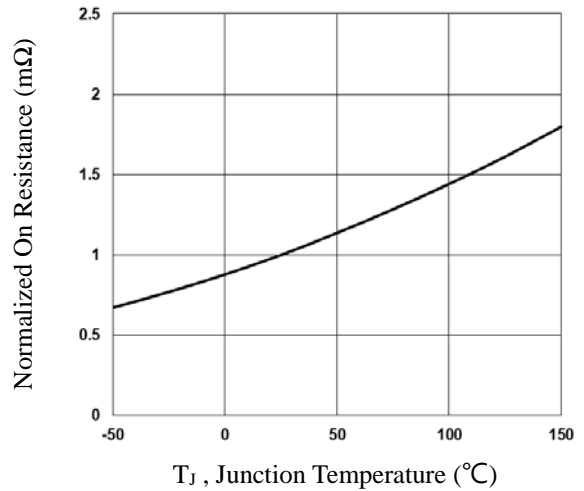


Fig.2 Normalized $R_{DS(on)}$ vs. T_J

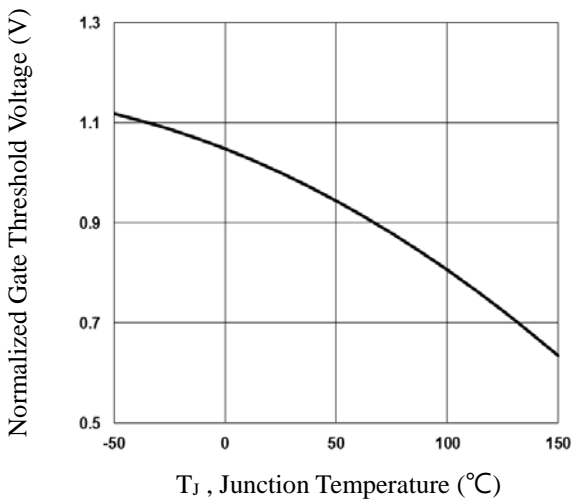


Fig.3 Normalized V_{th} vs. T_J

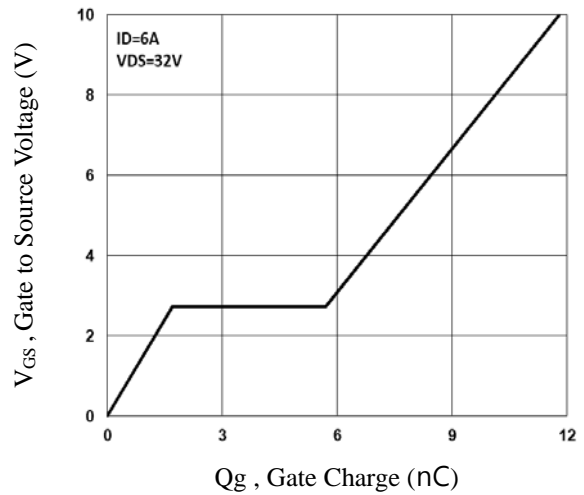


Fig.4 Gate Charge Waveform

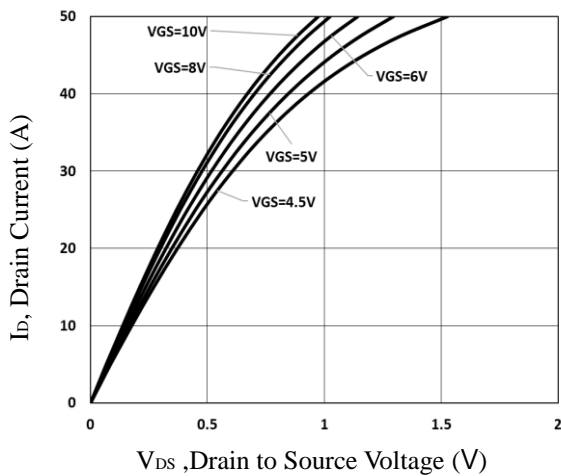


Fig.5 Typical Output Characteristics

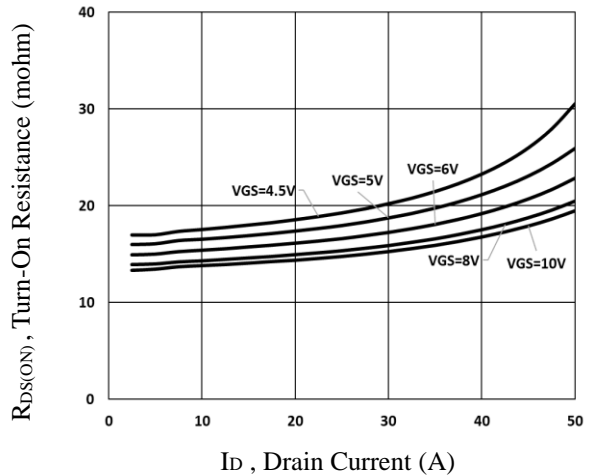


Fig.6 Turn-On Resistance vs. I_D

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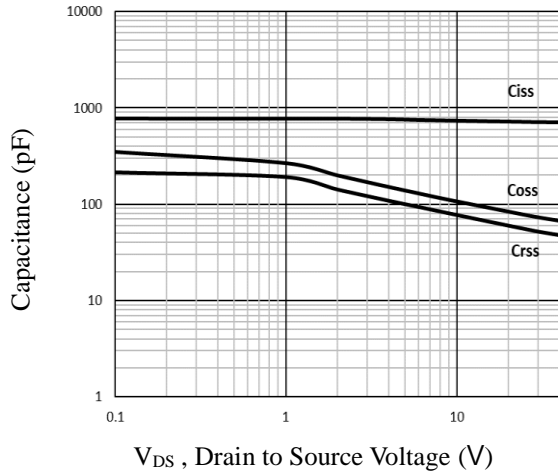


Fig.7 Capacitance Characteristics

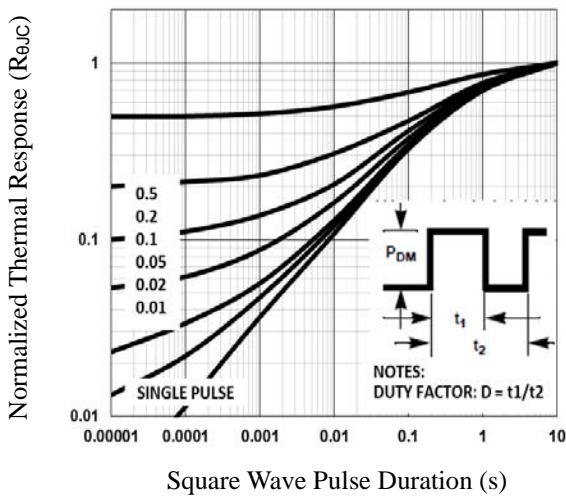


Fig.8 Normalized Transient Impedance

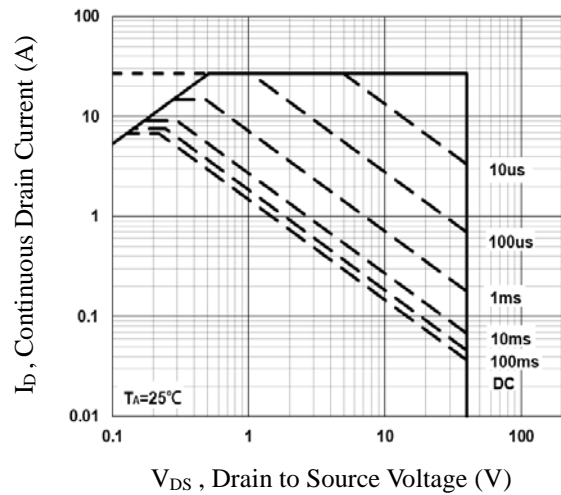


Fig.9 Maximum Safe Operation Area

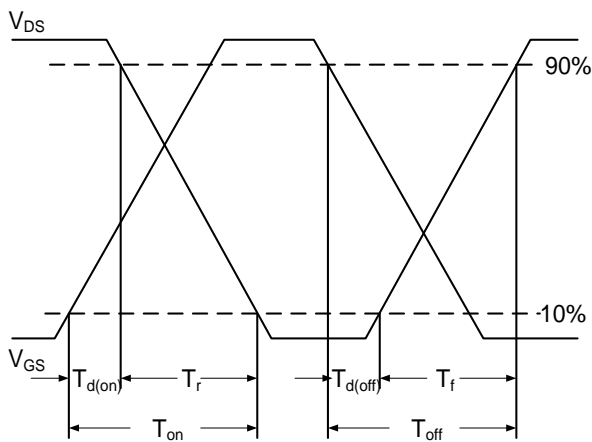


Fig.10 Switching Time Waveform

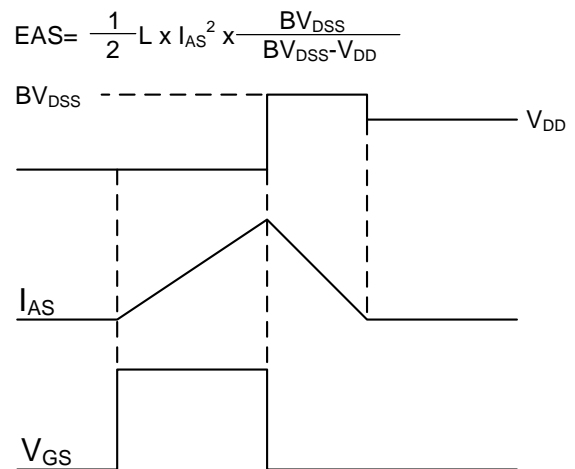
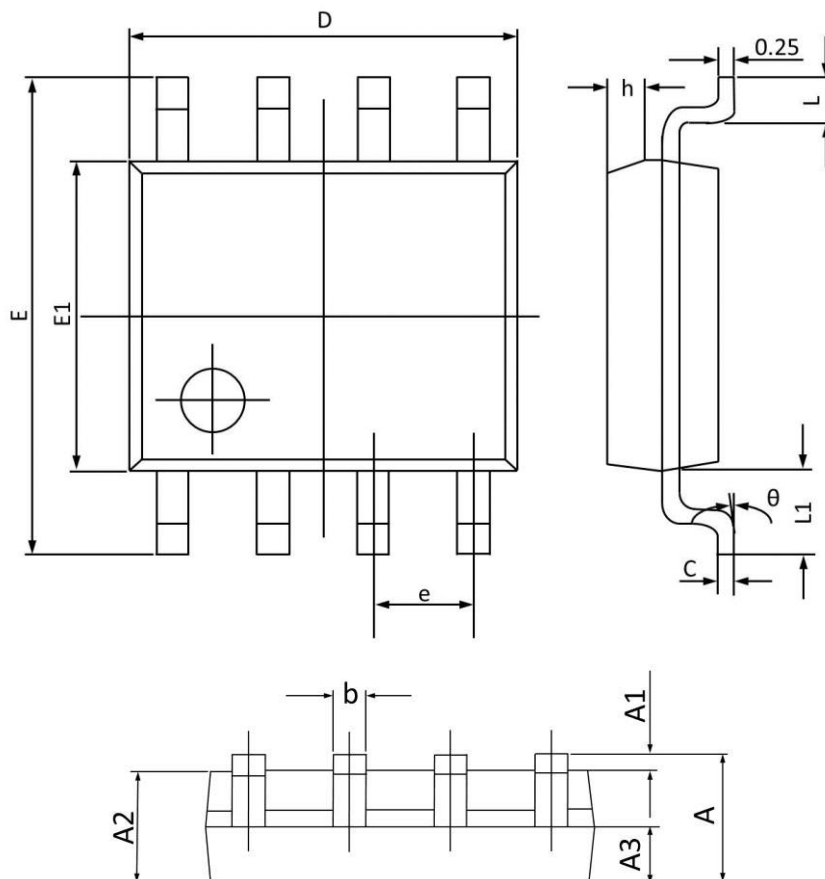


Fig.11 EAS Waveform

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SOP-8 PACKAGE INFORMATION



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.350	1.750	0.053	0.068
A1	0.100	0.250	0.004	0.009
A2	1.300	1.500	0.052	0.059
A3	0.600	0.700	0.024	0.027
b	0.390	0.480	0.016	0.018
c	0.210	0.260	0.009	0.010
D	4.700	5.100	0.186	0.200
E	5.800	6.200	0.229	0.244
E1	3.700	4.100	0.146	0.161
e	1.270(BSC)		0.050(BSC)	
h	0.250	0.500	0.010	0.019
L	0.500	0.800	0.019	0.031
L1	1.050(BSC)		0.041(BSC)	
θ	0°	8°	0°	8°